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plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/311.ccls. 430/312,394.cor. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 12 1717 430/312,394.ccls. not 430/312,394.cor. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT;			photopolymer\$7) and (etch or etched or		
(perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/311.ccls. 331 430/312,394.cor. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;			etching or etchant) and ((doubles of		
or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/311.ccls. 331 430/312,394.cor. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; 12 1717 430/312,394.ccls. not 430/312,394.cor. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;			/perpendiculars3 or cross\$3 or interlac\$3	1 2011 - 1000	
semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adjrandom adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/311.ccls. 331 430/312,394.cor. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; 12 1717 430/312,394.ccls. not 430/312,394.cor. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;			or intertwin\$3 or row or column)) and		
memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/311.ccls. 331 430/312,394.cor. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;			semiconduct\$3 and (stor\$3 or capacit\$4 or		
expos\$3)) and develop\$4) and (dynamic adjrandom adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/311.ccls. 331 430/312,394.cor. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;			memor\$5)) and ((line\$2 or parallel) same		
((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/311.ccls. 430/312,394.cor. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT;		1.	expos\$3)) and develop\$4) and (dynamic adj		
proximity) or (line with short\$5))) and 430/311.ccls. 430/312,394.cor. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;			random adj access or DRAM or memory)) and		
10 331 430/311.ccls. 430/312,394.cor. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;			((round\$3 with corner) or (optical with		
10 331 430/312,394.cor. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; 2003/02/10 18:			A30/311 cols		
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; 2003/02/10 18:	10	331		USPAT;	2003/02/10 18:34
DERWENT; IBM_TDB USPAT; 2003/02/10 18:	1 - 0				
12 1717 430/312,394.ccls. not 430/312,394.cor. IBM_TDB USPAT; 2003/02/10 18:					
1717 430/312,394.ccls. not 430/312,394.cor. USPAT; 2003/02/10 18:	ŧ				
1/1/ 430/312,394.0013. NOU 430/312/391.001.	1	1	420/212 204 colo		2003/02/10 18:52
I US-PGPUB: I	12	1717	430/312,394.CCIS. NOT 430/312,394.COF.	US-PGPUB;	1000,02,20 20.02
EPO; JPO;	1			1	
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IBM TDB	i			IBM TDB	

13	3071	(430/311-313,394.ccls. not	USPAT;	2003/02/10 19:19
,	, 30/1	430/312,394.ccls. not 430/312,394.cor.)	US-PGPUB;	,
		and pd>20021204	EPO; JPO;	
İ		and particular.	DERWENT;	į
			IBM TDB	
14	76	(430/311-313,394.ccls. not	USPAT;	2003/02/10 19:20
13	"	430/312,394.ccls. not 430/312,394.cor.)	US-PGPUB;	
		not @pd<=20021204	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
! <u>_</u>	6	(("5425848") or ("5817242") or ("6027595")	USPAT;	2002/10/29 18:38
1		or ("5512131") or ("5900160") or	US-PGPUB;	
ļ		("5925259")).PN.	JPO	
i –	146	430/311-313,394.ccls. and (interlace\$ or	USPAT;	2002/10/21 16:13
		intertwine\$ or double adj expos\$)	US-PGPUB;	
			JPO	
-	1	"5604059".PN.	USPAT	2002/10/21 14:40
-	1	430/311-313,394.ccls. and (interlac\$ or	EPO;	2003/02/10 18:15
		intertwin\$ or double adj expos\$)	DERWENT;	
			IBM_TDB	0000 (00 (10 10 16
_	146	430/311-313,394.ccls. and (interlac\$ or	USPAT;	2003/02/10 18:16
		intertwin\$ or double adj expos\$)	US-PGPUB;	
	ļ		JPO	2002/10/21 18:09
i –	1	"6042998".PN.	USPAT	2002/10/21 18:03
-	1	"5989952".PN.	USPAT	2002/10/21 18:15
-	1	"5841143".PN.	USPAT	2002/10/21 18:13
-	4951	430/311-313,394.ccls.	USPAT;	2003/02/10 18.17
			US-PGPUB; EPO; JPO;	
			DERWENT;	
1			IBM TDB	
1		(1) the second s	USPAT;	2002/11/21 13:23
-	1481	<pre>(photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant)</pre>	US-PGPUB;	2002/11/21 10:10
		and ((doubl\$3 or plural\$4) same expos\$)	EPO; JPO;	
		same (perpendicular\$3 or cross\$3 or	IBM_TDB	
		interlac\$3 or intertwin\$3)	15.1_155	
	600	((photoresist or resist or photopolymer\$7)	USPAT;	2002/11/21 13:55
-	698	and (etch or etched or etching or etchant)	US-PGPUB;	
		and ((doubl\$3 or plural\$4) same expos\$)	EPO; JPO;	
		same (perpendicular\$3 or cross\$3 or	IBM_TDB	
		interlac\$3 or intertwin\$3)) and	_	
		semiconduct\$3 and (stor\$3 or capacit\$4)		
1_	541	1	USPAT;	2002/11/21 13:56
	3.12	photopolymer\$7) and (etch or etched or	US-PGPUB;	
		etching or etchant) and ((doubl\$3 or	EPO; JPO;	
į		plural\$4) same expos\$) same	IBM_TDB	
ĺ		(perpendicular\$3 or cross\$3 or interlac\$3		
		or intertwin\$3)) and semiconduct\$3 and		
		(stor\$3 or capacit\$4)) and ((line\$2 or		
		parallel) same expos\$3)		0000/11/01 10 11
_	398	((((photoresist or resist or	USPAT;	2002/11/21 13:56
		photopolymer\$7) and (etch or etched or	US-PGPUB;	
1		etching or etchant) and ((doubl\$3 or	EPO; JPO;	
}		plural\$4) same expos\$) same	IBM_TDB	
1		(perpendicular\$3 or cross\$3 or interlac\$3		
i		or intertwin\$3)) and semiconduct\$3 and		
		(stor\$3 or capacit\$4)) and ((line\$2 or		
i i		parallel) same expos\$3)) and develop\$4	поращ	2002/11/21 13:57
-	66	(((((photoresist or resist or	USPAT;	2002/11/21 13:3/
1		photopolymer\$7) and (etch or etched or	US-PGPUB; EPO; JPO;	
		etching or etchant) and ((doub1\$3 or	1	
		plural\$4) same expos\$) same	IBM_TDB	
		(perpendicular\$3 or cross\$3 or interlac\$3		1
T'	1	or intertwin\$3)) and semiconduct\$3 and	1	*
		(stor\$3 or capacit\$4)) and ((line\$2 or		
		parallel) same expos\$3)) and develop\$4)		
		and (dynamic adj random adj access or		
T.	1	DRAM)	J	

			,	
-	769	<pre>((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and</pre>	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/21 13:56
;		semiconduct\$3 and (stor\$3 or capacit\$4 or		
		memor\$5)		0000/11/01 12.56
	602	<pre>(((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3</pre>	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/21 13:56
		or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)		0000 (11 (01 12 57
	438	photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/21 13:57
	74	or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4 (((((photoresist or resist or	USPAT;	2002/11/22 11:52
_	, 4	photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and	US-PGPUB; EPO; JPO; IBM_TDB	
	221	(stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM)	USPAT;	2002/11/22 11:55
_	331	photopolymer\$7) and (etch or etched or etching or etchant) and ((doub1\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3	US-PGPUB; EPO; JPO; IBM_TDB	2002/11/22 11/00
		or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adjrandom adj access or DRAM or memory)		2002/11/22 12:25
-	62	<pre>((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3</pre>	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2002/11/22 13:35
		or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and (line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))		
_	4	<pre>(((((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and</pre>	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/02/10 18:19
		semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and		
		((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/312.ccls.		

				0000 (00 (10 10 00)
-	2	((((((photoresist or resist or	USPAT;	2003/02/10 18:22
		photopolymer\$7) and (etch or etched or	US-PGPUB;	
		etching or etchant) and ((doub1\$3 or	EPO; JPO;	
		plural\$4) same expos\$) same	IBM_TDB	
!		(perpendicular\$3 or cross\$3 or interlac\$3		
,		or intertwin\$3 or row or column)) and		1
!		semiconduct\$3 and (stor\$3 or capacit\$4 or		1
		memor\$5)) and ((line\$2 or parallel) same		
		expos\$3)) and develop\$4) and (dynamic adj		
		random adj access or DRAM or memory)) and		
!		((round\$3 with corner) or (optical with		
1		proximity) or (line with short\$5))) and		
}		430/394.ccls.		
_	3		USPAT;	2003/02/10 18:23
-	3	photopolymer\$7) and (etch or etched or	US-PGPUB;	
!		etching or etchant) and ((doubl\$3 or	EPO; JPO;	
		plural\$4) same expos\$) same	IBM TDB	
!		(perpendicular\$3 or cross\$3 or interlac\$3		
1		or intertwin\$3 or row or column)) and		
		semiconduct\$3 and (stor\$3 or capacit\$4 or		
		semiconducts and (stores or parallel) same		
		memor\$5)) and ((line\$2 or parallel) same		[
1		expos\$3)) and develop\$4) and (dynamic adj		
		random adj access or DRAM or memory)) and		
		((round\$3 with corner) or (optical with		
		proximity) or (line with short\$5))) and		
		430/313.ccls.	rianam.	2003/02/10 18:24
-	3		USPAT;	2003/02/10 18:24
		photopolymer\$7) and (etch or etched or	US-PGPUB;	
		etching or etchant) and ((doubl\$3 or	EPO; JPO;	
		plural\$4) same expos\$) same	IBM_TDB	ļ
		(perpendicular\$3 or cross\$3 or interlac\$3		
	l	or intertwin\$3 or row or column)) and		1
		semiconduct\$3 and (stor\$3 or capacit\$4 or		
		memor\$5)) and ((line\$2 or parallel) same		
		expos\$3)) and develop\$4) and (dynamic adj		1
		random adj access or DRAM or memory)) and		
		((round\$3 with corner) or (optical with		
i		proximity) or (line with short\$5))) and		
		430/311.ccls.		

			UCDAM.	2003/02/10 18:26
-	57	((((((photoresist or resist or	USPAT; US-PGPUB;	2003/02/10 18:20
		photopolymer\$7) and (etch or etched or	EPO; JPO;	
		etching or etchant) and ((doub1\$3 or	IBM TDB	1
İ	1	plural\$4) same expos\$) same	1017-100	
		(perpendicular\$3 or cross\$3 or interlac\$3	1	
1		or intertwin\$3 or row or column)) and	i	
		<pre>semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same</pre>	1	į
•		expos\$3)) and ((line\$2 or pararier) same expos\$3)) and develop\$4) and (dynamic adj		
		random adj access or DRAM or memory)) and		
1		((round\$3 with corner) or (optical with		
•		proximity) or (line with short\$5)) not		
		(((((((photoresist or resist or		
		photopolymer\$7) and (etch or etched or		
		etching or etchant) and ((doubl\$3 or		
		plural\$4) same expos\$) same		
		(perpendicular\$3 or cross\$3 or interlac\$3		
		or intertwin\$3 or row or column)) and		1
		semiconduct\$3 and (stor\$3 or capacit\$4 or		
		memor\$5)) and ((line\$2 or parallel) same		1
į	1	expos\$3)) and develop\$4) and (dynamic adj		
		random adj access or DRAM or memory)) and		
		((round\$3 with corner) or (optical with		
]	proximity) or (line with short\$5))) and		
1		430/312.ccls.) not (((((((photoresist or		į
1	1	resist or photopolymer\$7) and (etch or		1
1		etched or etching or etchant) and		<u> </u>
		((doubl\$3 or plural\$4) same expos\$) same		İ
		(perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and		
		semiconduct\$3 and (stor\$3 or capacit\$4 or		
		memor\$5)) and ((line\$2 or parallel) same		_
		expos\$3)) and develop\$4) and (dynamic adj		
		random adj access or DRAM or memory)) and		
		((round\$3 with corner) or (optical with		
		proximity) or (line with short\$5))) and		
	1	430/394.ccls.) not ((((((photoresist or		
		resist or photopolymer\$7) and (etch or		
		etched or etching or etchant) and		
		((doubl\$3 or plural\$4) same expos\$) same		
		(perpendicular\$3 or cross\$3 or interlac\$3		
		or intertwin\$3 or row or column)) and		
		semiconduct\$3 and (stor\$3 or capacit\$4 or		
		memor\$5)) and ((line\$2 or parallel) same	1	
		expos\$3)) and develop\$4) and (dynamic adj		
		random adj access or DRAM or memory)) and		
		((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and		
}		430/313.ccls.) not (((((((photoresist or		
i		resist or photopolymer\$7) and (etch or	1	
		etched or etching or etchant) and		
		((doubl\$3 or plural\$4) same expos\$) same		
	1	(perpendicular\$3 or cross\$3 or interlac\$3		
		or intertwin\$3 or row or column)) and		
1		semiconduct\$3 and (stor\$3 or capacit\$4 or		
	ļ	memor\$5)) and ((line\$2 or parallel) same		
		expos\$3)) and develop\$4) and (dynamic adj		
		random adi access or DRAM or memory)) and		
		((round\$3 with corner) or (optical with		
1		proximity) or (line with short\$5))) and		
		430/311.ccls.)	HCDATE.	2002/12/04 10:24
-	5004	430/311-313,394.ccls.	USPAT; US-PGPUB;	2002/12/04 10.24
1	1		EPO; JPO;	<u> </u>
			DERWENT;	
1			IBM TDB	
1				

- 1	1	(430/311-313,394.ccls. and (interlac\$ or	·	2002/12/04 10:03
		intertwin\$ or double adj expos\$)) not	US-PGPUB;	
į	1	(((((((photoresist or resist or	EPO; JPO;	
	İ	photopolymer\$7) and (etch or etched or	IBM_TDB	1
		etching or etchant) and ((doub1\$3 or		
-		plural\$4) same expos\$) same	!	
		(perpendicular\$3 or cross\$3 or interlac\$3	İ	
1		or intertwin\$3 or row or column)) and	İ	
		semiconduct\$3 and (stor\$3 or capacit\$4 or		
	1	memor\$5)) and ((line\$2 or parallel) same		
		expos\$3)) and develop\$4) and (dynamic adj	į	
		random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with		1
1		proximity) or (line with short\$5)) not	_ 4	
		((((((((photoresist or resist or	1	8.0 1
		photopolymer\$7) and (etch or etched or	1	
		etching or etchant) and ((doubl\$3 or		
		plural\$4) same expos\$) same	1	
		(perpendicular\$3 or cross\$3 or interlac\$3		
		or intertwin\$3 or row or column)) and		
		semiconduct\$3 and (stor\$3 or capacit\$4 or		
		memor\$5)) and ((line\$2 or parallel) same		
		expos\$3)) and develop\$4) and (dynamic adj		
	1	random adj access or DRAM or memory)) and		
		((round\$3 with corner) or (optical with		
		proximity) or (line with short\$5))) and		
		430/312.ccls.) not (((((((photoresist or		
		resist or photopolymer\$7) and (etch or		
	Ì	etched or etching or etchant) and		
	1	((doubl\$3 or plural\$4) same expos\$) same		1
		(perpendicular\$3 or cross\$3 or interlac\$3		
		or intertwin\$3 or row or column)) and		
		semiconduct\$3 and (stor\$3 or capacit\$4 or		
		memor\$5)) and ((line\$2 or parallel) same		
		expos\$3)) and develop\$4) and (dynamic adj		
		random adj access or DRAM or memory)) and		
		((round\$3 with corner) or (optical with		
		proximity) or (line with short\$5))) and		
		430/394.ccls.) not (((((((photoresist or resist or photopolymer\$7) and (etch or		
}		etched or etching or etchant) and		
		((doubl\$3 or plural\$4) same expos\$) same		
		(perpendicular\$3 or cross\$3 or interlac\$3		
		or intertwin\$3 or row or column)) and		
		semiconduct\$3 and (stor\$3 or capacit\$4 or		
		memor\$5)) and ((line\$2 or parallel) same		
		expos\$3)) and develop\$4) and (dynamic adj		
		random adj access or DRAM or memory)) and		
		((round\$3 with corner) or (optical with		
		proximity) or (line with short\$5))) and		
		430/313.ccls.) not ((((((photoresist or	•	
		resist or photopolymer\$7) and (etch or		
		etched or etching or etchant) and		
		((doub1\$3 or plural\$4) same expos\$) same		
		(perpendicular\$3 or cross\$3 or interlac\$3		
		or intertwin\$3 or row or column)) and		
		semiconduct\$3 and (stor\$3 or capacit\$4 or		
		memor\$5)) and ((line\$2 or parallel) same		
		expos\$3)) and develop\$4) and (dynamic adj		
		random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with		
1		proximity) or (line with short\$5))) and		
1	2000	430/311.ccls.)) 430/312,394.ccls.	USPAT;	2002/12/04 10:27
-	2009	430/312/394.0013.	US-PGPUB;	
			EPO; JPO;	
•			DERWENT;	
1			IBM TDB	

- 1	324	430/312,394.cor.	USPAT;	2003/02/10 18:34
			US-PGPUB;	i
:			EPO; JPO;	
i			DERWENT;	
;			IBM_TDB	2000/10/04 12:36
	13	("4591540" "5286584" "5308741"	USPAT	2002/12/04 12:36
		"5340700" "5424154" "5532090"		
i		"5563012" "5620816" "5702868"		
		"5804339" "5807649" "5851707"		
		"5863677").PN.	USPAT;	2003/02/10 18:51
-	1685	430/312,394.ccls. not 430/312,394.cor.	US-PGPUB;	2003/02/10 10:01
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
1	2005	430/311-313,394.ccls. not	USPAT;	2003/02/10 19:12
-	2995	430/311-313,594.cc13. not 430/312,394.cor.	US-PGPUB;	
		430/312,394.6613. 1106 130/322/0744	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
	2	(("5103274") or ("5120671")).PN.	USPAT;	2002/12/07 14:02
1		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB	
1_	3	(("6184151") or ("5955244") or	USPAT;	2002/12/10 14:44
		("20010028422")).PN.	US-PGPUB	